

OTHER PUBLICATIONS

- Sakai, A. et al., "Defect structure in selectively grown GaN films with low threading dislocation density", *Appl. Phys. Lett.* 71, (16), 2259, Oct. 20, 1997.
- Liliental-Weber, Z. et al., "TEM study of defects in laterally overgrown GaN layers", *MRS Internet J. Nitride Semicond. Res. Res. 4S1* (1998) G4.6.
- Liliental-Weber, Z. et al., "Microstructure of laterally overgrown GaN layers", *J. Appl. Phys.* 89 (12), 7833, Jun. 15, 2001.
- Zheleva, T. et al., "Pendo-Epitaxy: A new approach for lateral growth of gallium nitride films", *J. Elect. Mat.* 28 (4) 1999, Nov. 12, 1998.
- Fini, P. et al., "Maskless lateral epitaxial overgrowth of GaN on sapphire", *Mater. Res. Soc. Symp. Proc.* 572, (1999) 315.
- Davis, R.F. et al., "Pendo-epitaxial growth of thin films of gallium nitride and related materials and their characterization", *J. Crystal Growth* 225, (2001) pp. 134-140.
- Trinkaus, H. et al., "Strain relaxation mechanism for hydrogen-implanted $\text{Si}_{1-x}\text{Ge}_x/\text{Si}(100)$ heterostructures", *Appl. Phys. Lett.* 76 (24), 3552, Jun. 12, 2000.
- Luysberg, M. et al., "Effect of helium ion implantation and annealing on the relaxation behavior of pseudomorphic $\text{Si}_{1-x}\text{Ge}_x$ buffer layers on Si (100) substrates", *J. Appl. Phys.*, 92 (8) 4290, Oct. 15, 2002.
- Reinhardt, Karen A. et al., "Handbook of silicon wafer cleaning technology", 2nd edition, Elsevier Science & Technology Book, Jan. 2008, ISBN-13: 9780815515548, 1.4 "Overview of wafer cleaning and surface conditioning technology", pp. 21-29.
- Miller, N. et al., "Low-temperature grown compositionally graded InGaN films", *Phys Stat. Sol (C)*, vol. 5, No. 6, 1866-1869, (2008), Sep. 15, 2007.
- Wei-Kan Chu et al., "Backscattering Spectrometry", Academic Press Inc., New York, 1978.
- Fichtner, P.F.P. et al., "Nucleation and growth of platelet bubble structures in He implanted silicon", *Nucl. Instr. And Meth. In Phys. Res.*, B 136-138 (1998) 460.
- Ziegler, J.F. et al., "The Stopping and Range of Ions in Solids", Pergamon Press, Oxford, 1985, vol. 1.
- Semond, F. et al., "GaN grown on Si(111) substrate: From two-dimensional growth to quantum well assessment", *Appl. Phys. Lett.* 75 (1999) 82, Jul. 5, 1999.
- Chu, W.K. et al., "Rutherford backscattering spectrometry: reminiscences and progresses", *Materials Chemistry and Physics* 46 (1996) 183-188.
- Liliental-Weber et al., 2007 APS March Meeting, Session A40: Semiconductors: Growth of Nitrides, conference presentation slides: Redirecting of misfit dislocations from AlN/Si interface into the substrate, Mar. 5, 2007.
- Maltez et al., "GaN/AlN/Si(111) Heteroepitaxy on He Ion implanted Si(111) Substrates—RBS/C studies", Universidade Federal Do Rio Grande Do Sol, IBMM 08, Dresden, Germany, conference presentation slides, Sep. 25-27, 2007.
- Liliental-Weber et al., "Propagation of misfit dislocations from AlN/Si interface into Si", *Journal of Crystal Growth* 310 (2008) 3917-3923, Jun. 7, 2008.
- Liliental-Weber et al., "Propagation of misfit dislocations from AlN/Si interface into Si", Conference presentation slides, Sep. 25-27, 2007.

* cited by examiner